



# 100V 28mΩ Dual N-Ch Power MOSFET

## Features

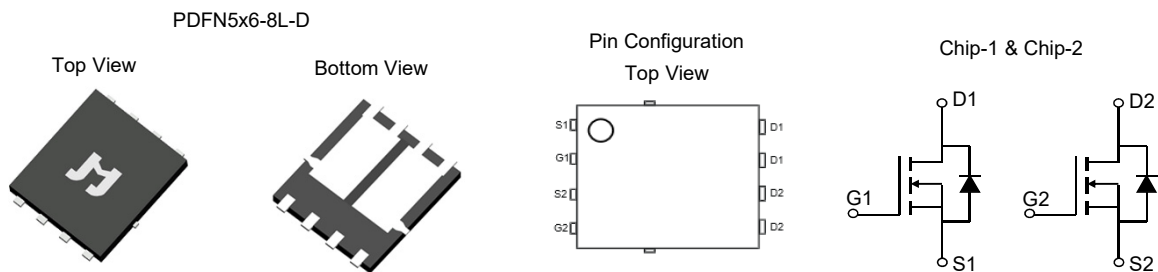
- Low  $R_{DS(ON)}$
- Low Gate Charge
- 100% UIS Tested, 100%  $R_g$  Tested
- Pb-free Lead Plating
- Halogen-free and RoHS-compliant

## Product Summary

Parameter	Value	Unit
$V_{DS}$	100	V
$V_{GS(th\_Typ)}$	2.0	V
$I_D$ (@ $V_{GS} = 10V$ ) <sup>(1)</sup>	18.4	A
$R_{DS(ON\_Typ)}$ (@ $V_{GS} = 10V$ )	28	mΩ
$R_{DS(ON\_Typ)}$ (@ $V_{GS} = 4.5V$ )	40	mΩ

## Applications

- Power Management in Telecom., Industrial Automation, CE
- Current Switching in DC/DC & AC/DC Sub-systems
- Motor Driving in Power Tool, E-vehicle, Robotics

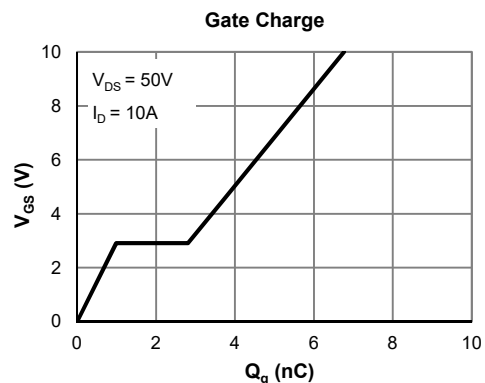
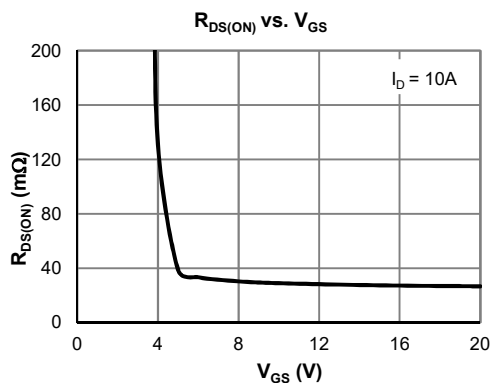


## Ordering Information

Device	Package	# of Pins	Marking	MSL	$T_J$ (°C)	Media	Quantity (pcs)
JMSL1040AGD-13	PDFN5x6-8L-D	8	L1040AD	1	-55 to 150	13-inch Reel	3000

## Absolute Maximum Ratings (@ $T_A = 25^\circ C$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DS}$	100	V
Gate-to-Source Voltage	$V_{GS}$	±20	V
Continuous Drain Current <sup>(1)</sup>	$I_D$	$T_C = 25^\circ C$	18.4
		$T_C = 100^\circ C$	11.6
Pulsed Drain Current <sup>(2)</sup>	$I_{DM}$	73	A
Avalanche Current <sup>(3)</sup>	$I_{AS}$	15.0	A
Avalanche Energy <sup>(3)</sup>	$E_{AS}$	11.3	mJ
Power Dissipation <sup>(4)</sup>	$P_D$	$T_C = 25^\circ C$	23
		$T_C = 100^\circ C$	9.1
Junction & Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	°C





**Electrical Characteristics** (@  $T_J = 25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Conditions	Min.	Typ.	Max.	Unit
<b>STATIC PARAMETERS</b>						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	100			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 80\text{V}, V_{GS} = 0\text{V}$ $T_J = 55^\circ\text{C}$			1.0 5.0	$\mu\text{A}$
Gate-Body Leakage Current	$I_{GSS}$	$V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	1.2	2.0	3.0	V
Static Drain-Source ON-Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{V}, I_D = 10\text{A}$		28	36	$\text{m}\Omega$
		$V_{GS} = 4.5\text{V}, I_D = 6\text{A}$		40	52	$\text{m}\Omega$
Forward Transconductance	$g_{FS}$	$V_{DS} = 5\text{V}, I_D = 10\text{A}$		28		S
Diode Forward Voltage	$V_{SD}$	$I_S = 1\text{A}, V_{GS} = 0\text{V}$		0.70	1.0	V
Diode Continuous Current	$I_S$	$T_C = 25^\circ\text{C}$			23	A

<b>DYNAMIC PARAMETERS <sup>(5)</sup></b>						
Input Capacitance	$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 50\text{V}, f = 1\text{MHz}$		363		pF
Output Capacitance	$C_{oss}$			85		pF
Reverse Transfer Capacitance	$C_{rss}$			3.0		pF
Gate Resistance	$R_g$	$V_{GS} = 0\text{V}, V_{DS} = 0\text{V}, f = 1\text{MHz}$		2.6		$\Omega$

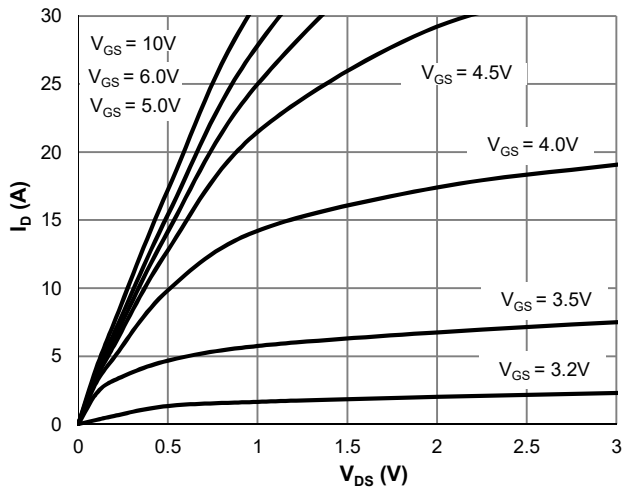
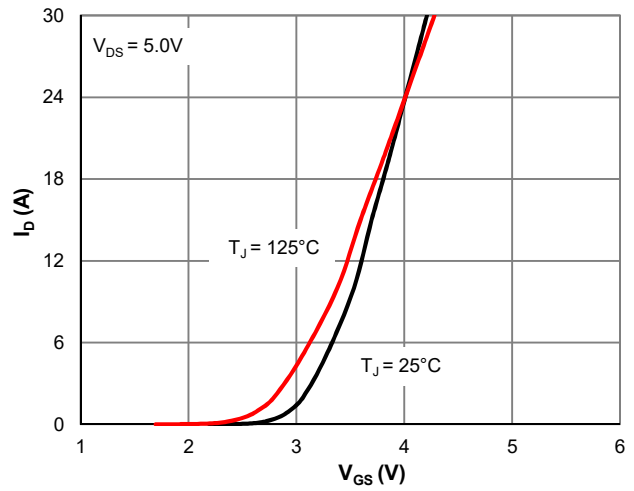
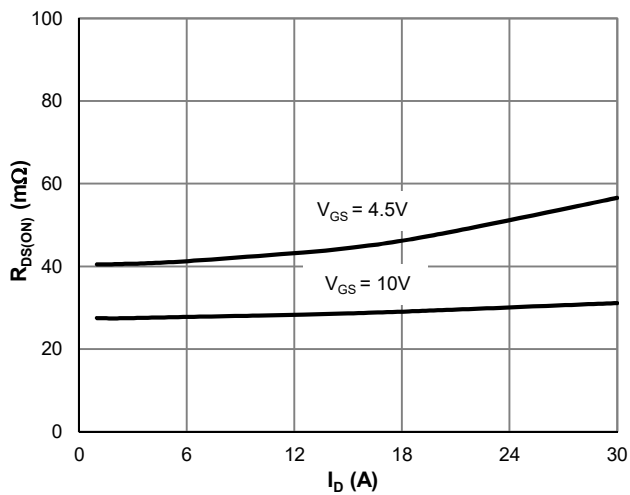
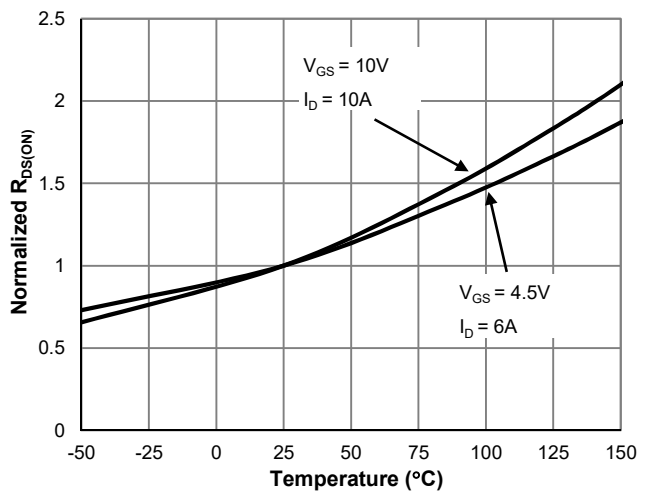
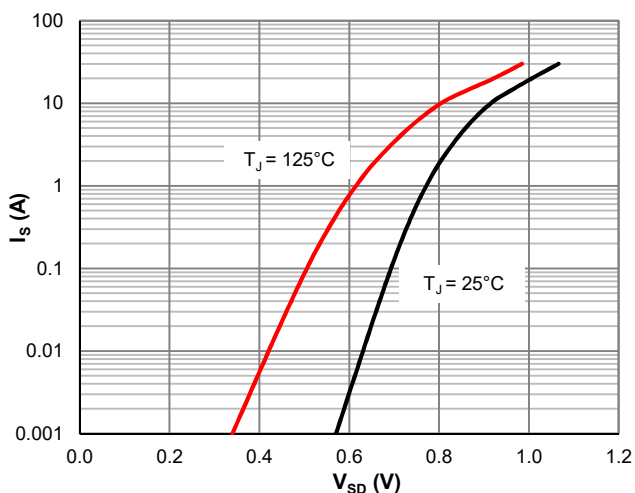
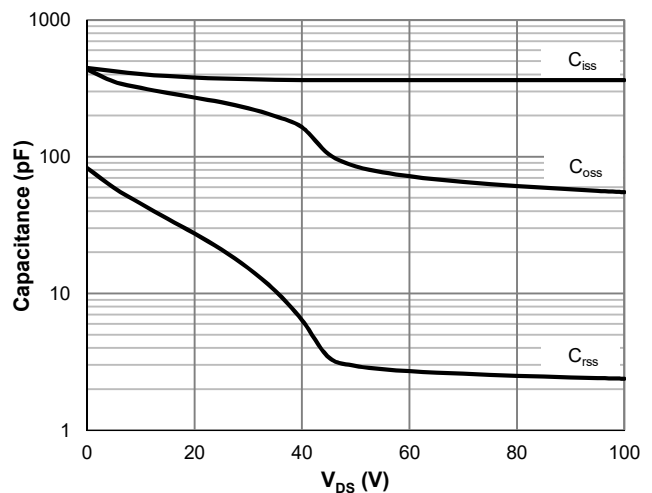
<b>SWITCHING PARAMETERS <sup>(5)</sup></b>						
Total Gate Charge (@ $V_{GS} = 10\text{V}$ )	$Q_g$	$V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 50\text{V}, I_D = 10\text{A}$		6.8		nC
Total Gate Charge (@ $V_{GS} = 4.5\text{V}$ )	$Q_g$			3.7		nC
Gate Source Charge	$Q_{gs}$			1.0		nC
Gate Drain Charge	$Q_{gd}$			1.8		nC
Turn-On DelayTime	$t_{D(on)}$			4.9		ns
Turn-On Rise Time	$t_r$	$V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ $R_L = 5.0\Omega, R_{GEN} = 6\Omega$		16.6		ns
Turn-Off DelayTime	$t_{D(off)}$			11.2		ns
Turn-Off Fall Time	$t_f$			4.9		ns
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 10\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		33		ns
Body Diode Reverse Recovery Charge	$Q_{rr}$	$I_F = 10\text{A}, dI_F/dt = 100\text{A}/\mu\text{s}$		45		nC

**Thermal Performance**

Parameter	Symbol	Typ.	Max.	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	48	58	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	4.2	5.5	$^\circ\text{C}/\text{W}$

**Notes:**

1. Computed continuous current assumes the condition of  $T_{J\_Max}$  while the actual continuous current depends on the thermal & electro-mechanical application board design.
2. This single-pulse measurement was taken under  $T_{J\_Max} = 150^\circ\text{C}$ .
3. This single-pulse measurement was taken under the following condition [ $L = 100\mu\text{H}, V_{GS} = 10\text{V}, V_{DS} = 50\text{V}$ ] while its value is limited by  $T_{J\_Max} = 150^\circ\text{C}$ .
4. The power dissipation  $P_D$  is based on  $T_{J\_Max} = 150^\circ\text{C}$ .
5. This value is guaranteed by design hence it is not included in the production test.

**Typical Electrical & Thermal Characteristics**

**Figure 1: Saturation Characteristics**

**Figure 2: Transfer Characteristics**

**Figure 3:  $R_{DS(ON)}$  vs. Drain Current**

**Figure 4:  $R_{DS(ON)}$  vs. Junction Temperature**

**Figure 5: Body-Diode Characteristics**

**Figure 6: Capacitance Characteristics**

Typical Electrical & Thermal Characteristics

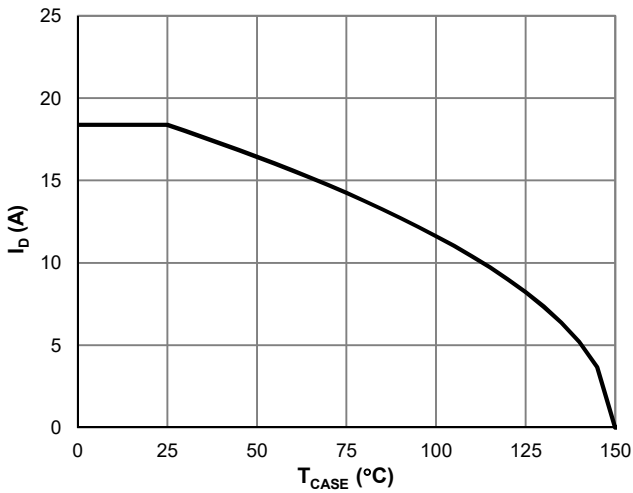


Figure 7: Current De-rating

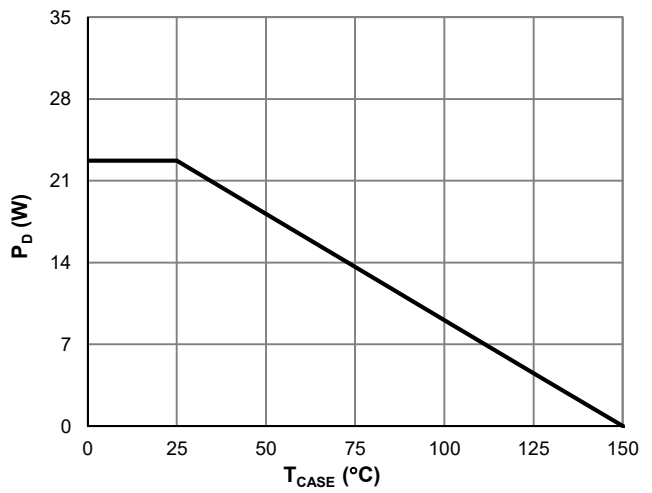


Figure 8: Power De-rating

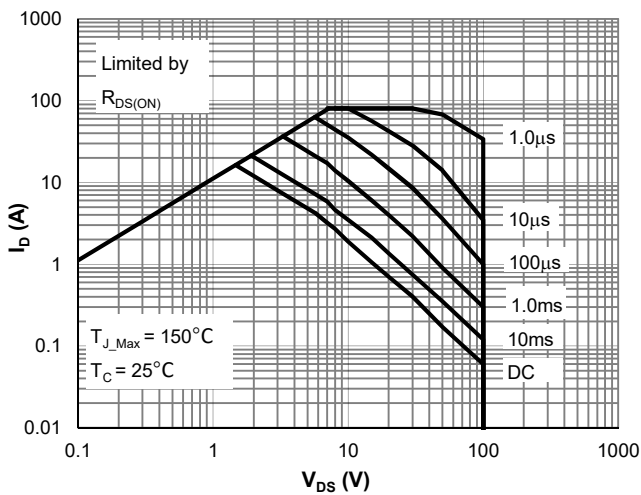


Figure 9: Maximum Safe Operating Area

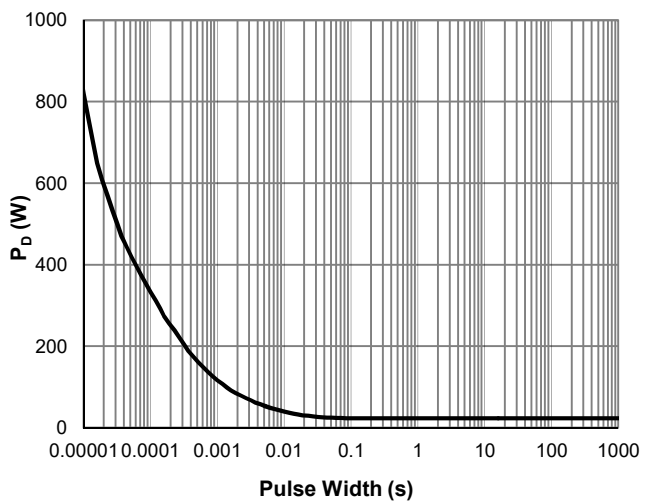


Figure 10: Single Pulse Power Rating, Junction-to-Case

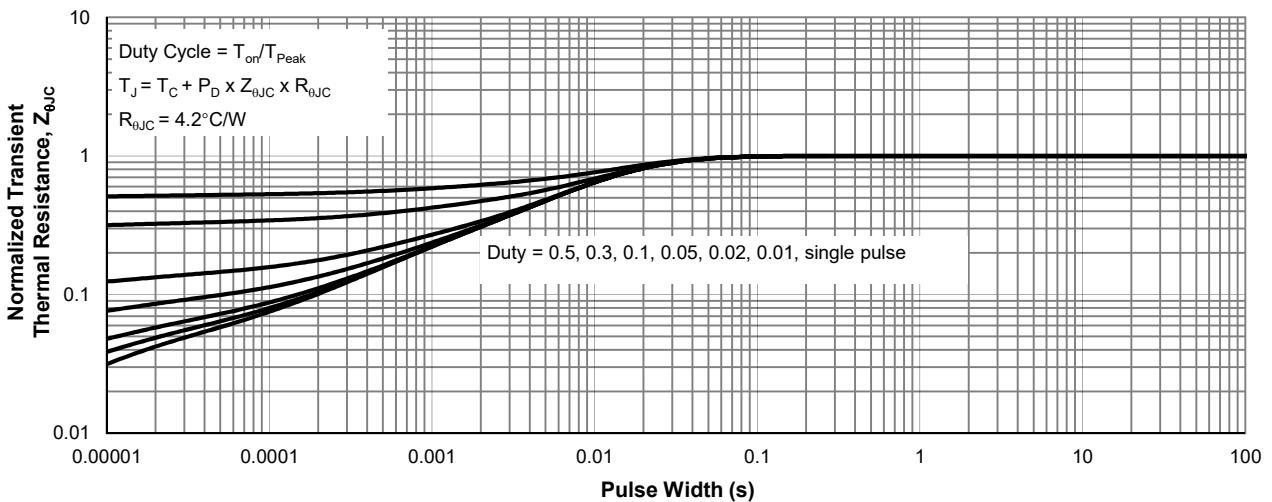
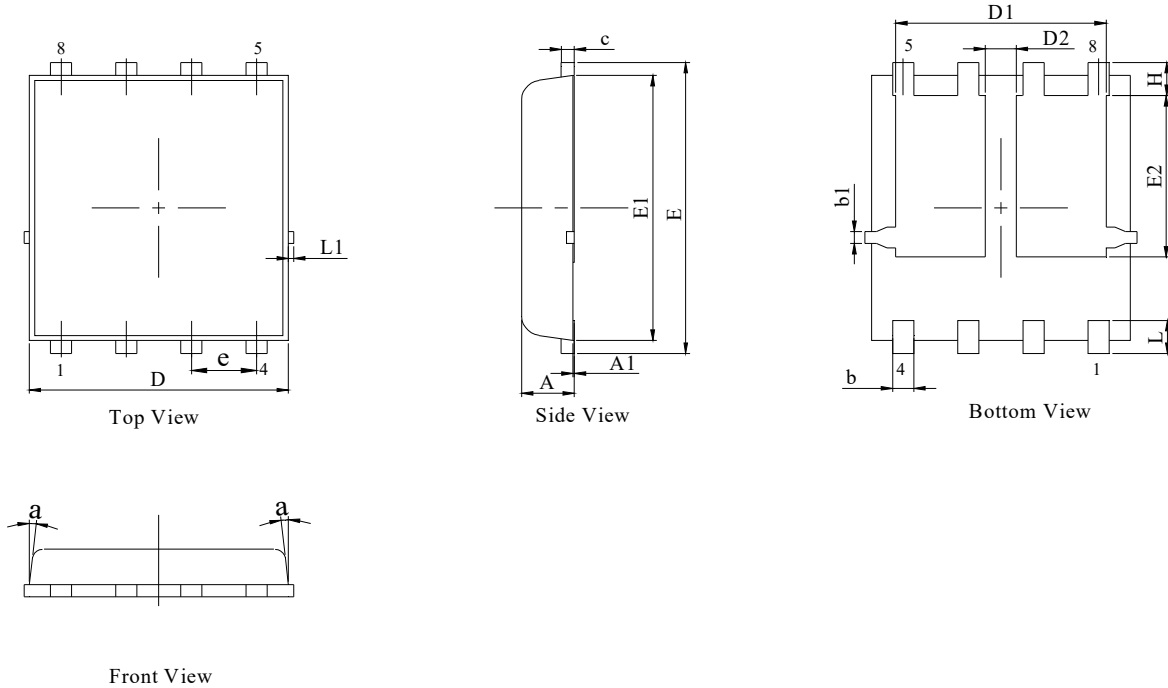
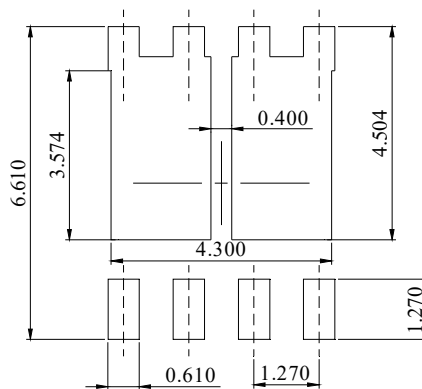


Figure 11: Normalized Maximum Transient Thermal Impedance

**PDFN5x6-8L-D Package Information**
**Package Outline**

**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ASME Y 14.5M,1994.
2. ALL DIMNESIONS IN MILLIMETER (ANNGL E IN DEGREE).
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM.	MILLIMETER		
	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	-	0.10
b	0.31	0.41	0.51
b1	0.15	0.25	0.35
c	0.23	-	0.33
D	4.95	5.05	5.15
D1	4.00	4.10	4.20
D2	0.50	0.60	0.70
E	6.05	6.15	6.25
E1	5.50	5.60	5.70
E2	3.31	3.41	3.51
e	1.27BSC		
H	0.60	0.70	0.80
L	0.50	0.70	0.80
L1	-	-	0.125
a	-	-	12°

**Recommended Soldering Footprint**


DIMENSIONS: MILLIMETERS